WIN SOURCE ELECTRONICS

THE DATASHEET OF

MRF7S27130HR3

Document Number: MRF7S27130H
Rev. 2, 3/2011

RoHS

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

MRF7S27130HR3
MRF7S27130HSR3

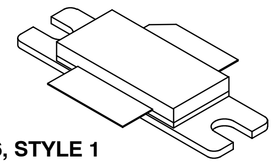
Designed for WiMAX base station applications with frequencies up to 2700 MHz. Suitable for WiMAX, WiBro, BWA, and OFDM multicarrier Class AB and Class C amplifier applications.

- Typical WiMAX Performance: V_{DD} = 28 Volts, I_{DQ} = 1500 mA, P_{out} = 23 Watts Avg., f = 2700 MHz, 802.16d, 64 QAM $^3/_4$, 4 bursts, 7 MHz Channel Bandwidth, Input Signal PAR = 9.5 dB @ 0.01% Probability on CCDF.
  - Power Gain — 16.5 dB
  - Drain Efficiency — 20%
  - Device Output Signal PAR — 8.2 dB @ 0.01% Probability on CCDF
  - ACPR @ 5.25 MHz Offset — -49 dBc in 0.5 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 32 Vdc, 2600 MHz, 105 Watts CW Output Power

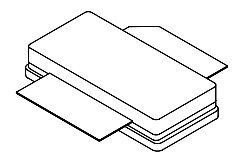
Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units, 56 mm Tape Width, 13 inch Reel. For R5 Tape and Reel option, see p. 14.

**2500-2700 MHz, 23 W AVG., 28 V
WiMAX
LATERAL N-CHANNEL
RF POWER MOSFETs**



**CASE 465-06, STYLE 1
NI-780
MRF7S27130HR3**



**CASE 465A-06, STYLE 1
NI-780S
MRF7S27130HSR3**

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C
CW Operation @ T_C = 25°C Derate above 25°C	CW	150 0.83	W W/°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 80°C, 104 W CW Case Temperature 69°C, 23 W CW	$R_{\theta JC}$	 0.32 0.36	°C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at http://www.freescale.com/rf. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes - AN1955.

freescale semiconductor

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1B (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 65 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 348 μAdc)	$V_{GS(th)}$	1.2	2	2.7	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 1500 mAdc)	$V_{GS(Q)}$	—	2.7	—	Vdc
Fixture Gate Quiescent Voltage (1) (V_{DD} = 28 Vdc, I_D = 1500 mAdc, Measured in Functional Test)	$V_{GG(Q)}$	4	5.4	7	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 3.4 Adc)	$V_{DS(on)}$	0.1	0.24	0.3	Vdc
Dynamic Characteristics (2)					
Reverse Transfer Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	10.4	—	pF
Output Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{oss}	—	711	—	pF
Input Capacitance (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc ± 30 mV(rms)ac @ 1 MHz)	C_{iss}	—	326	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 1500 mA, P_{out} = 23 W Avg., f = 2700 MHz, WiMAX Signal, 802.16d, 7 MHz Channel Bandwidth, 64 QAM $^3/_4$, 4 Bursts, PAR = 9.5 dB @ 0.01% Probability on CCDF. ACPR measured in 0.5 MHz Channel Bandwidth @ ±5.25 MHz Offset.

Characteristic	Symbol	Min	Typ	Max	Unit
Power Gain	G_{ps}	15	16.5	18.5	dB
Drain Efficiency	η_D	18	20	23	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	7.5	8.2	—	dB
Adjacent Channel Power Ratio	ACPR	—	-49	-46	dBc
Input Return Loss	IRL	—	-8	-5	dB

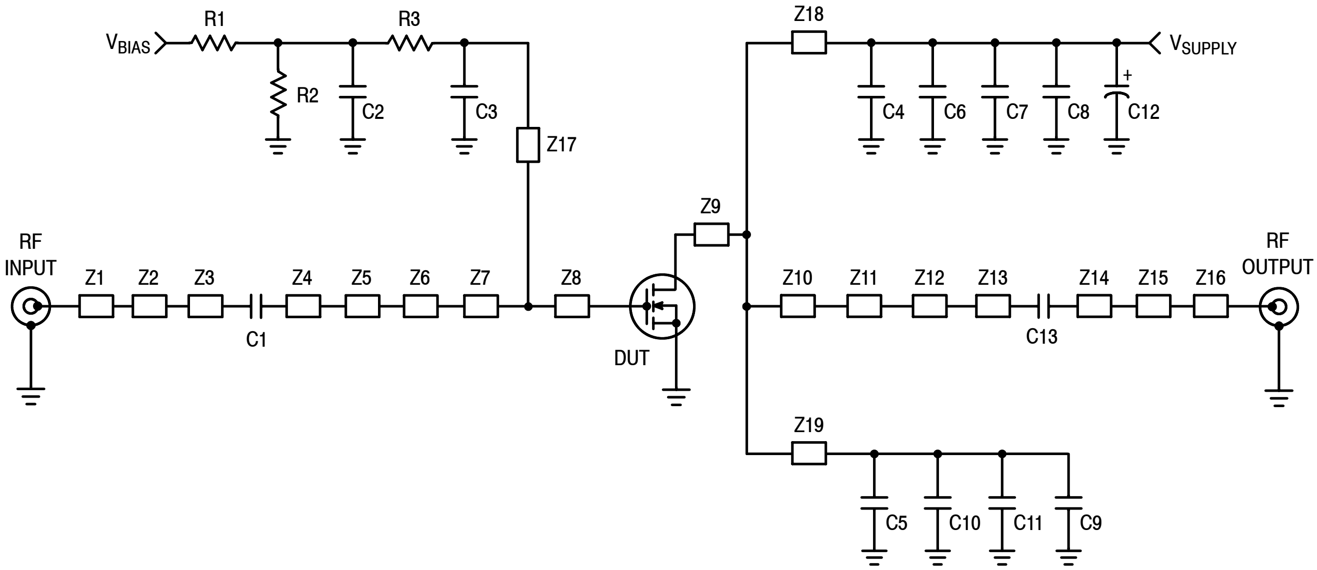
1. V_{GG} = 2 x $V_{GS(Q)}$. Parameter measured on Freescale Test Fixture, due to resistive divider network on the board. Refer to Test Circuit schematic.
2. Part internally matched both on input and output.

(continued)

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Typical Performances OFDM Signal (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 1500 mA, P_{out} = 23 W Avg., f = 2500 MHz and f = 2700 MHz, WiMAX Signal, OFDM Single-Carrier, 7 MHz Channel Bandwidth, 64 QAM $^3/_4$, 4 Bursts, PAR = 9.5 dB @ 0.01% Probability on CCDF.					
Mask System Type G @ P_{out} = 23 W Avg.	Mask				dBc
Point B at 3.5 MHz Offset		—	-27	—	
Point C at 5 MHz Offset		—	-40	—	
Point D at 7.4 MHz Offset		—	-44	—	
Point E at 14 MHz Offset		—	-60	—	
Point F at 17.5 MHz Offset		—	-60	—	
Relative Constellation Error @ P_{out} = 23 W Avg. (1)	RCE	—	-33	—	dB
Error Vector Magnitude (1) (Typical EVM Performance @ P_{out} = 23 W Avg. with OFDM 802.16d Signal Call)	EVM	—	2.2	—	% rms
Typical Performances (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 1500 mA, 2500-2700 MHz Bandwidth					
Video Bandwidth @ 105 W PEP P_{out} where IM3 = -30 dBc (Tone Spacing from 100 kHz to VBW) ΔIMD3 = IMD3 @ VBW frequency - IMD3 @ 100 kHz <1 dBc (both sidebands)	VBW	—	40	—	MHz
Gain Flatness in 200 MHz Bandwidth @ P_{out} = 23 W Avg.	G_F	—	1.2	—	dB
Average Deviation from Linear Phase in 200 MHz Bandwidth @ P_{out} = 105 W CW	Φ	—	135	—	°
Average Group Delay @ P_{out} = 105 W CW, f = 2600 MHz	Delay	—	1.5	—	ns
Part-to-Part Insertion Phase Variation @ P_{out} = 105 W CW, f = 2600 MHz, Six Sigma Window	$\Delta\Phi$	—	81.3	—	°
Gain Variation over Temperature (-30°C to +85°C)	ΔG	—	0.013	—	dB/°C
Output Power Variation over Temperature (-30°C to +85°C)	ΔP1dB	—	0.01	—	dB/°C

1. RCE = 20Log(EVM/100)



Z1	0.320″ x 0.084″ Microstrip	Z11	0.251″ x 0.084″ Microstrip
Z2	0.380″ x 0.240″ Microstrip	Z12	0.160″ x 0.162″ Microstrip
Z3	0.046″ x 0.084″ Microstrip	Z13	0.566″ x 0.084″ Microstrip
Z4	0.273″ x 0.084″ Microstrip	Z14	0.059″ x 0.084″ Microstrip
Z5	0.360″ x 0.600″ Microstrip	Z15	0.080″ x 0.123″ Microstrip
Z6	0.260″ x 0.394″ Microstrip	Z16	0.583″ x 0.084″ Microstrip
Z7	0.145″ x 0.922″ Microstrip	Z17*	0.950″ x 0.100″ Microstrip
Z8	0.455″ x 0.922″ Microstrip	Z18, Z19*	0.560″ x 0.100″ Microstrip
Z9	0.106″ x 0.716″ Microstrip	PCB	Taconic TLX8-0300, 0.030″, ε_r = 2.55
Z10	0.413″ x 0.716″ Microstrip		

* Variable for tuning

Figure 1. MRF7S27130HR3(HSR3) Test Circuit Schematic

Table 5. MRF7S27130HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1	2 pF Chip Capacitor	ATC100B2R0BT500XT	ATC
C2, C6, C7, C8, C9, C10, C11	10 μF, 50 V Chip Capacitors	C5750X5R1H106M	TDK
C3	3 pF Chip Capacitor	ATC100B3R0BT500XT	ATC
C4, C5	3.6 pF Chip Capacitors	ATC100B3R6BT500XT	ATC
C12	470 μF, 63 V Electrolytic Capacitor, Radial	EKME630ELL471MK255	Multicomp
C13	5.6 pF Chip Capacitor	ATC100B5R6BT500XT	ATC
R1, R2	2 KΩ, 1/4 W Chip Resistors	CRCW12062001FKEA	Vishay
R3	10 Ω, 1/4 W Chip Resistor	CRCW120610R1FKEA	Vishay

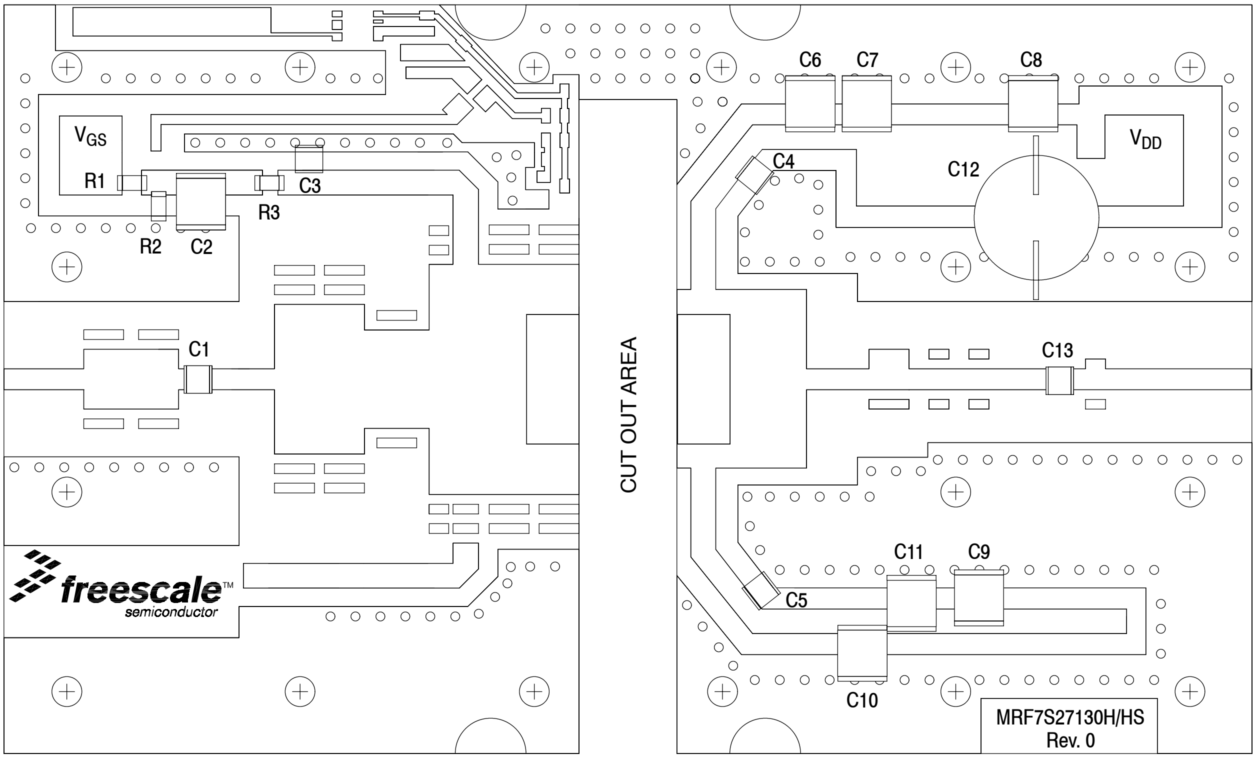


Figure 2. MRF7S27130HR3(HSR3) Test Circuit Component Layout

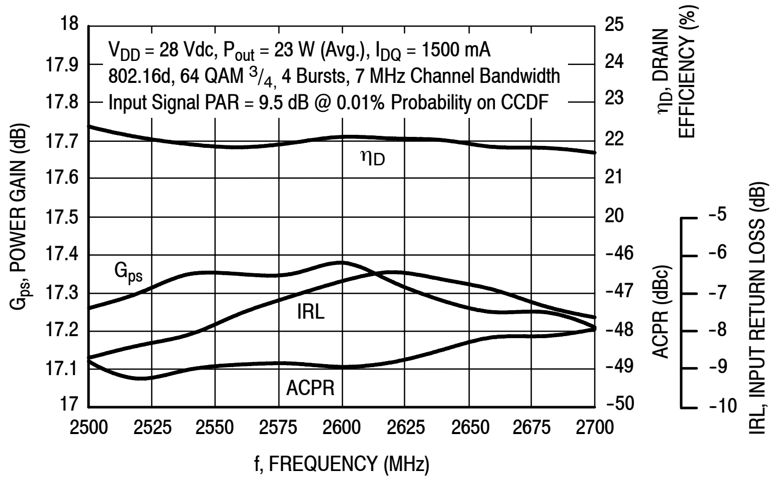


Figure 3. WiMAX Broadband Performance @ P_{out} = 23 Watts Avg.

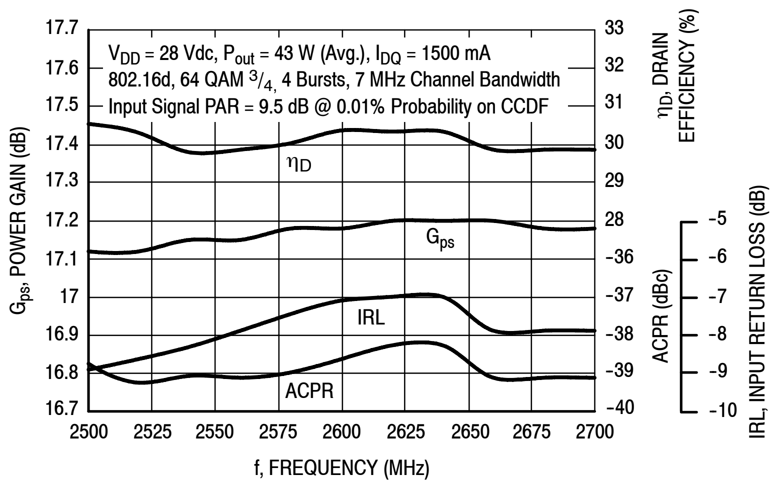


Figure 4. WiMAX Broadband Performance @ P_{out} = 43 Watts Avg.

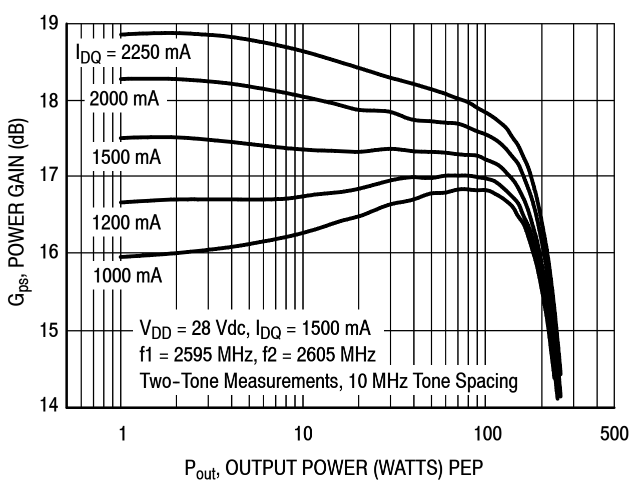


Figure 5. Two-Tone Power Gain versus Output Power

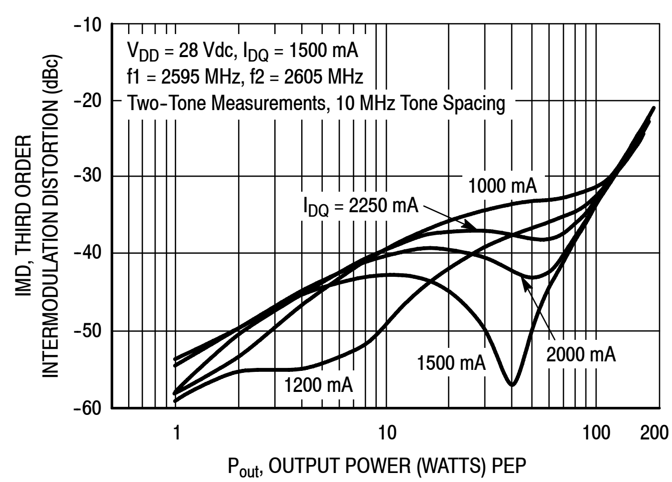


Figure 6. Third Order Intermodulation Distortion versus Output Power

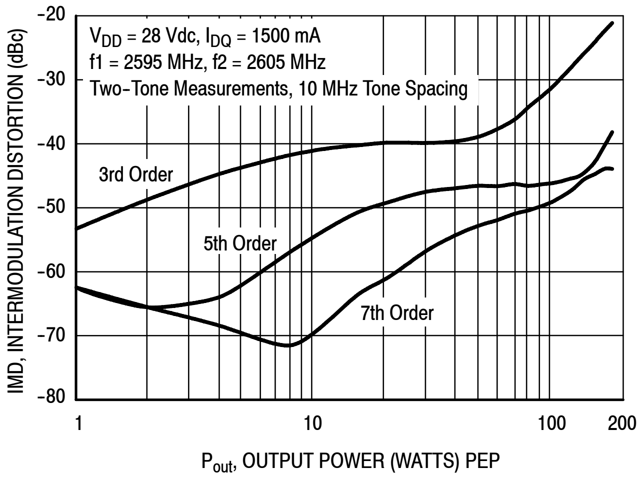


Figure 7. Intermodulation Distortion Products versus Output Power

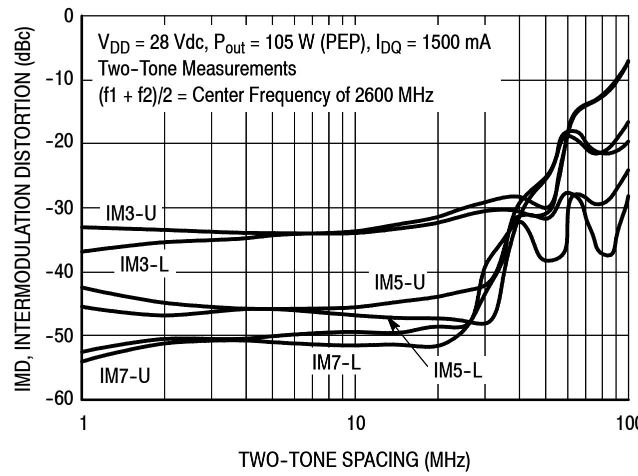


Figure 8. Intermodulation Distortion Products versus Tone Spacing

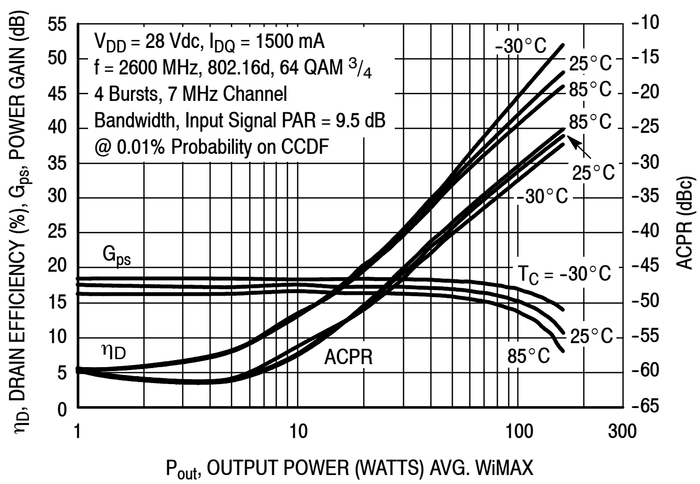


Figure 9. WiMAX, ACPR, Power Gain and Drain Efficiency versus Output Power

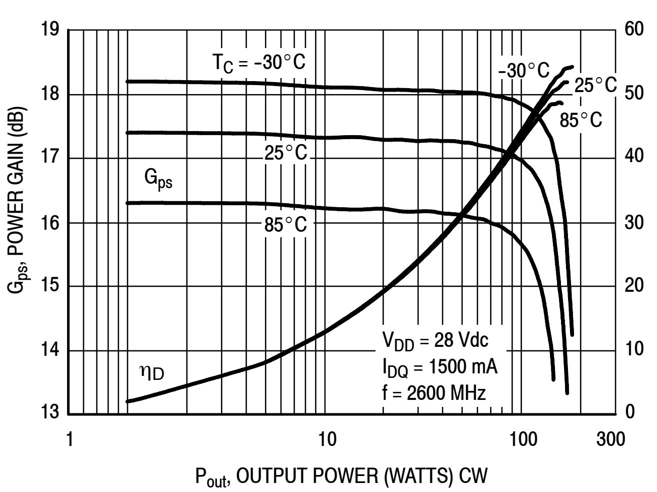


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

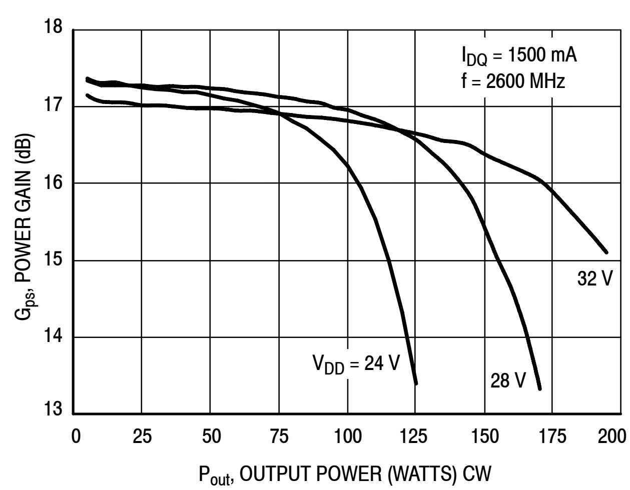


Figure 11. Power Gain versus Output Power

WiMAX TEST SIGNAL

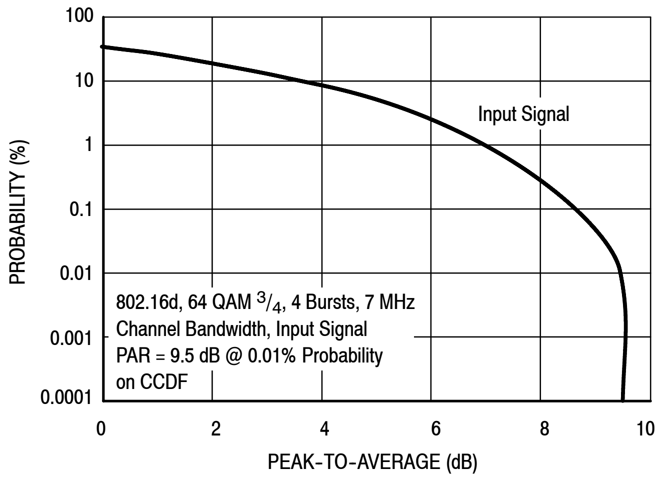


Figure 12. OFDM 802.16d Test Signal

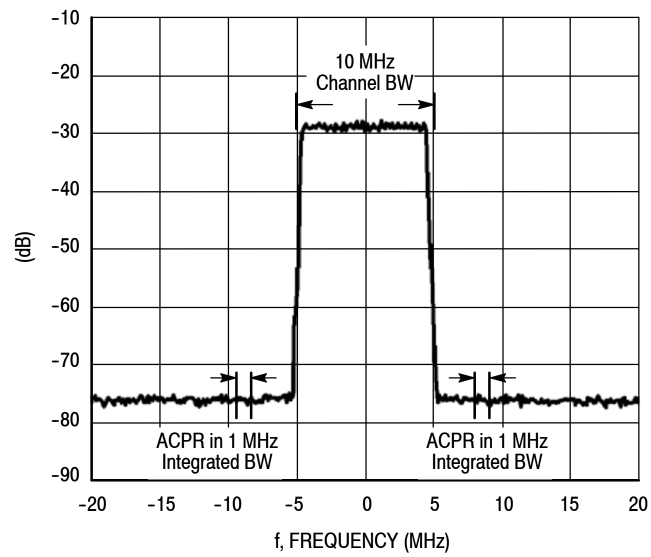
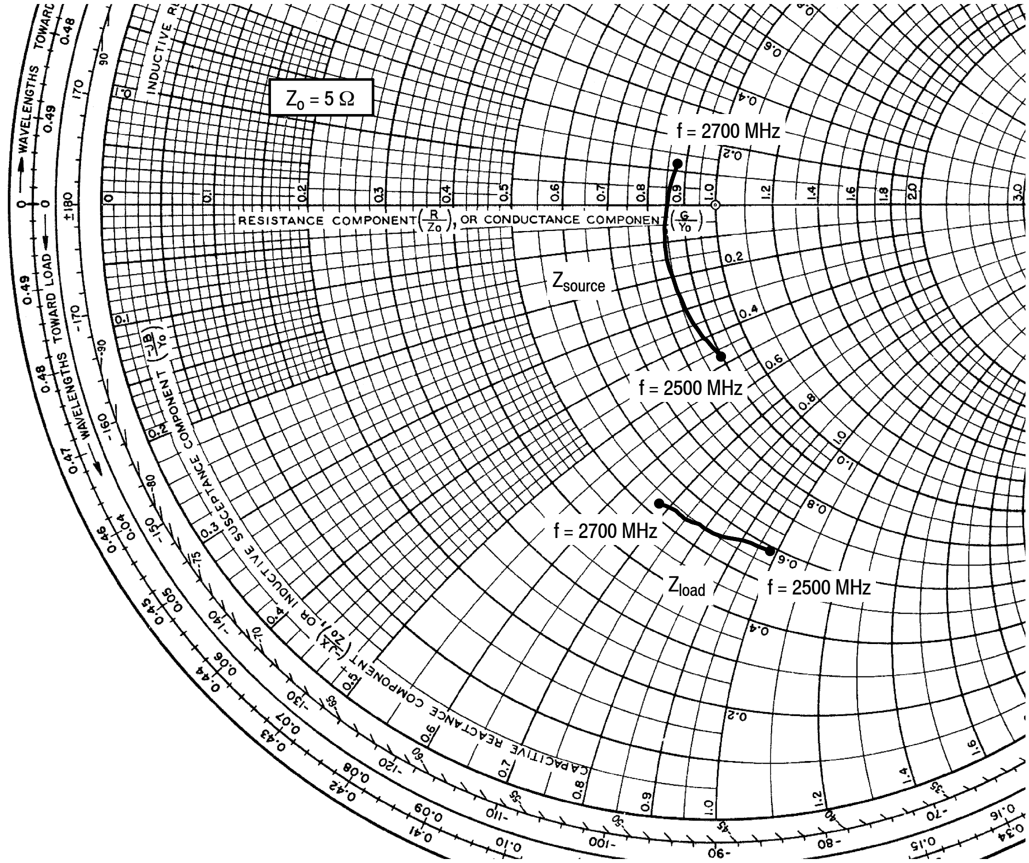


Figure 13. WiMAX Spectrum Mask Specifications



V_{DD} = 28 Vdc, I_{DQ} = 1500 mA, P_{out} = 23 W Avg.

f MHz	Z_{source} Ω	Z_{load} Ω
2500	4.499 – j2.335	2.936 – j4.876
2525	4.382 – j1.944	2.885 – j4.666
2550	4.294 – j1.567	2.838 – j4.467
2575	4.234 – j1.194	2.797 – j4.273
2600	4.209 – j0.820	2.763 – j4.084
2625	4.219 – j0.447	2.733 – j3.903
2650	4.248 – j0.090	2.706 – j3.732
2675	4.304 + j0.261	2.678 – j3.570
2700	4.390 + j0.612	2.652 – j3.410

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

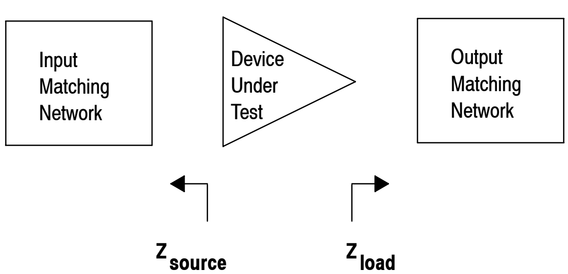
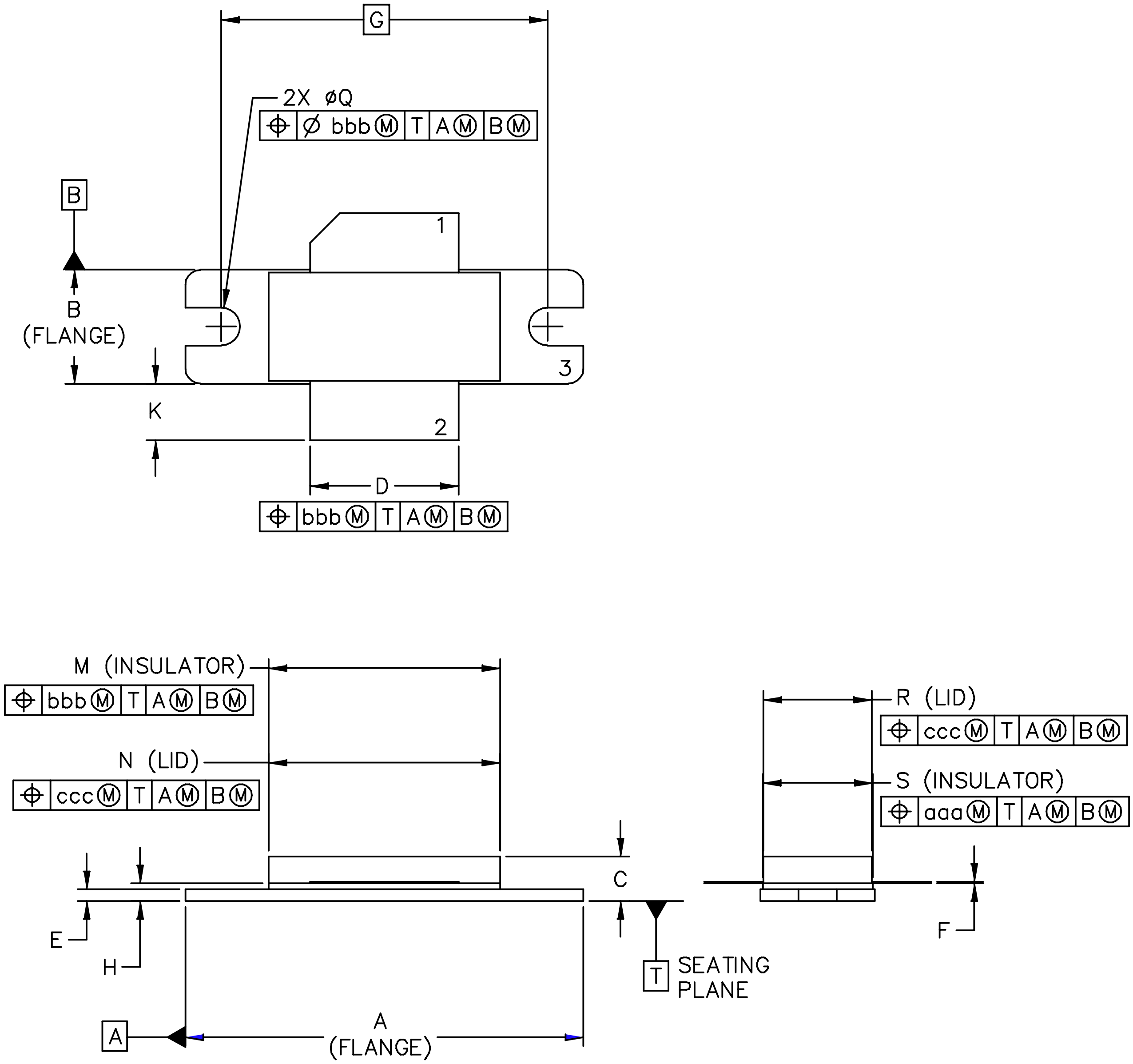


Figure 14. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M—1994.

2. CONTROLLING DIMENSION: INCH.

3. DELETED

4. DIMENSION H IS MEASURED .030 (.762) AWAY FROM PACKAGE BODY.

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

DIM	INCH MIN		INCH MAX	MILLIMETER MIN		MILLIMETER MAX	DIM	INCH MIN		INCH MAX	MILLIMETER MIN		MILLIMETER MAX
A	1.335	–	1.345	33.91	–	34.16	R	.365	–	.375	9.27	–	9.53
B	.380	–	.390	9.65	–	9.91	S	.365	–	.375	9.27	–	9.52
C	.125	–	.170	3.18	–	4.32	aaa	–	.005	–	–	0.127	–
D	.495	–	.505	12.57	–	12.83	bbb	–	.010	–	–	0.254	–
E	.035	–	.045	0.89	–	1.14	ccc	–	.015	–	–	0.381	–
F	.003	–	.006	0.08	–	0.15	–	–	–	–	–	–	–
G	1.100 BSC			27.94 BSC			–	–	–	–	–	–	–
H	.057	–	.067	1.45	–	1.7	–	–	–	–	–	–	–
K	.170	–	.210	4.32	–	5.33	–	–	–	–	–	–	–
M	.774	–	.786	19.66	–	19.96	–	–	–	–	–	–	–
N	.772	–	.788	19.6	–	20	–	–	–	–	–	–	–
Q	ø.118	–	ø.138	ø3	–	ø3.51	–	–	–	–	–	–	–

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	CASE NUMBER: 465–06	31 MAR 2005
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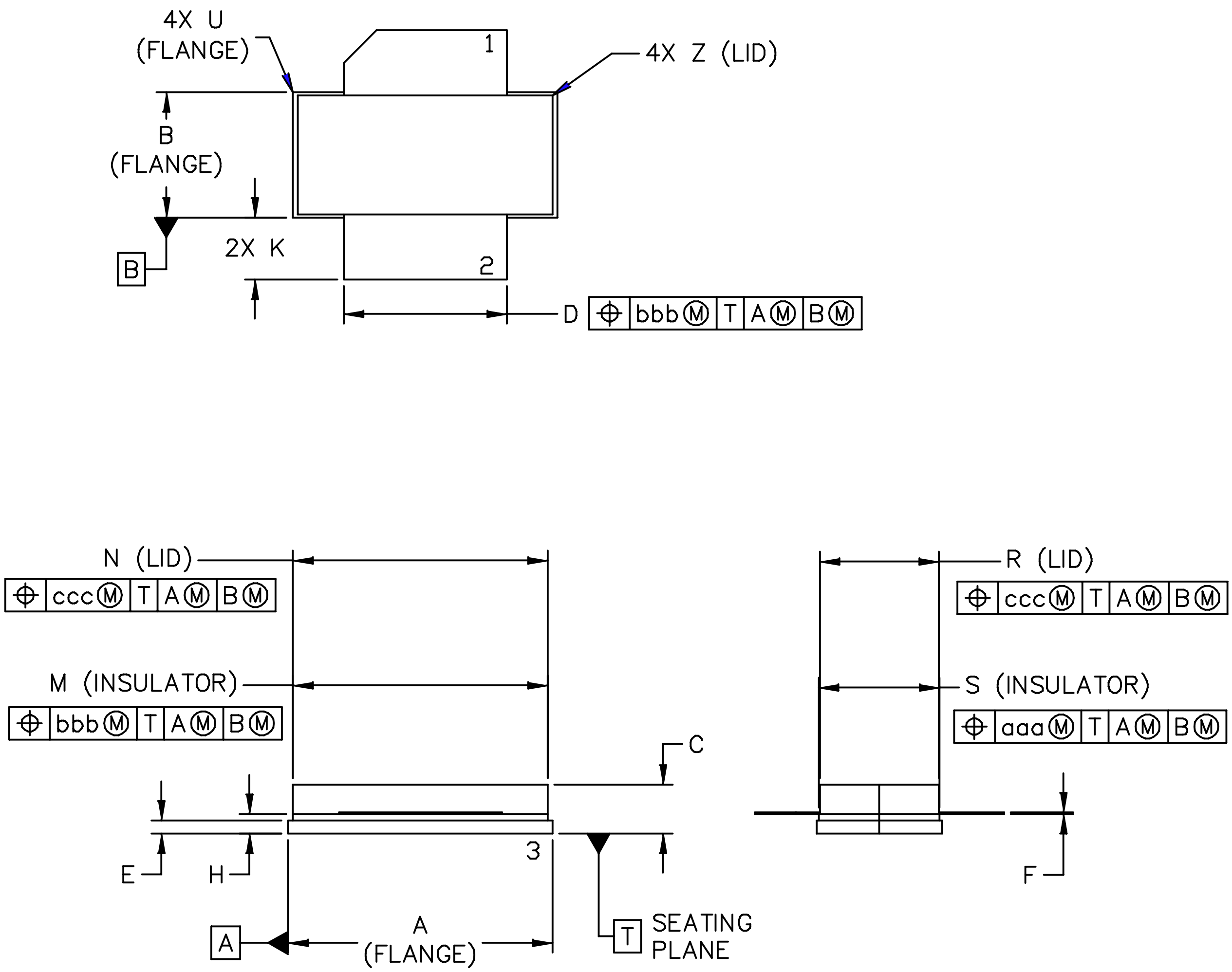

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	STANDARD: NON–JEDEC		

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M—1994.

2. CONTROLLING DIMENSION: INCH.

3. DELETED

4. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

DIM	INCH			MILLIMETER			DIM	INCH			MILLIMETER		
	MIN		MAX	MIN		MAX		MIN		MAX	MIN		MAX
A	.805	—	.815	20.45	—	20.7	U	—	—	.040	—	—	1.02
B	.380	—	.390	9.65	—	9.91	Z	—	—	.030	—	—	0.76
C	.125	—	.170	3.18	—	4.32	aaa	—	.005	—	—	0.127	—
D	.495	—	.505	12.57	—	12.83	bbb	—	.010	—	—	0.254	—
E	.035	—	.045	0.89	—	1.14	ccc	—	.015	—	—	0.381	—
F	.003	—	.006	0.08	—	0.15	—	—	—	—	—	—	—
H	.057	—	.067	1.45	—	1.7	—	—	—	—	—	—	—
K	.170	—	.210	4.32	—	5.33	—	—	—	—	—	—	—
M	.774	—	.786	19.61	—	20.02	—	—	—	—	—	—	—
N	.772	—	.788	19.61	—	20.02	—	—	—	—	—	—	—
R	.365	—	.375	9.27	—	9.53	—	—	—	—	—	—	—
S	.365	—	.375	9.27	—	9.52	—	—	—	—	—	—	—

	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
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	STANDARD: NON—JEDEC	

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model

For Software, do a Part Number search at http://www.freescale.com, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

R5 TAPE AND REEL OPTION

R5 Suffix = 50 Units, 56 mm Tape Width, 13 inch Reel.

The R5 tape and reel option for MRF7S27130H and MRF7S27130HS parts will be available for 2 years after release of MRF7S27130H and MRF7S27130HS. Freescale Semiconductor, Inc. reserves the right to limit the quantities that will be delivered in the R5 tape and reel option. At the end of the 2 year period customers who have purchased these devices in the R5 tape and reel option will be offered MRF7S27130H and MRF7S27130HS in the R3 tape and reel option.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Sept. 2007	• Initial Release of Data Sheet
1	Dec. 2008	• Modified Fig. 13 to display Input Signal only, p. 8 • Updated Fig. 14, WiMAX Spectrum Mask Specification, to reflect the distortion free input test signal versus the distortion loaded output signal, p. 8
2	Mar. 2011	• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN13628, p. 1, 2 • Fig. 12, MTTF versus Junction Temperature removed, p. 8. Refer to the device’s MTTF Calculator available at freescale.com/RFpower. Go to Design Resources > Software and Tools. • Added Electromigration MTTF Calculator and RF High Power Model availability to Product Software, p. 14

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